

/ Descriptions

SOP-8 P MOS

P-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

/ Features

$V_{DS}(V)=-30V$ $I_D=-5.0A$

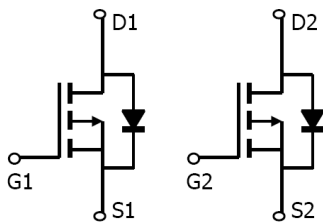
$R_{DS(ON)} < 65m\Omega (V_{GS}=-10V)$

$R_{DS(ON)} < 75m\Omega (V_{GS}=-4.5V)$

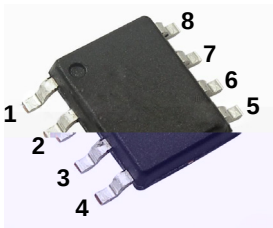
/ Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems and this device is suitable for use as a load switch or in PWM applications.

/ Equivalent Circuit



/ Pinning



PIN1	S2	PIN 2	G2	PIN 3	S1	PIN 4	G1
PIN 5	D1	PIN 6	D1	PIN 7	D2	PIN 8	D2

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	$I_D (T_a=25^{\circ}\text{C})$	-5.0	A
	$I_D (T_a=70^{\circ}\text{C})$	-4.2	A
Pulsed Drain Current ^B	I_{DM}	-20	A
Power Dissipation for Single Operation ^A	$P_D (T_a=25^{\circ}\text{C})$	2.0	W
	$P_D (T_a=70^{\circ}\text{C})$	1.4	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 +150	$^{\circ}\text{C}$
Thermal Resistance-Junction to Ambient ^A	$R_{\theta JA} \quad t \leq 10s$	62.5	$^{\circ}\text{C/W}$
	$R_{\theta JA}$	110	$^{\circ}\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	40	$^{\circ}\text{C/W}$

Note:

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

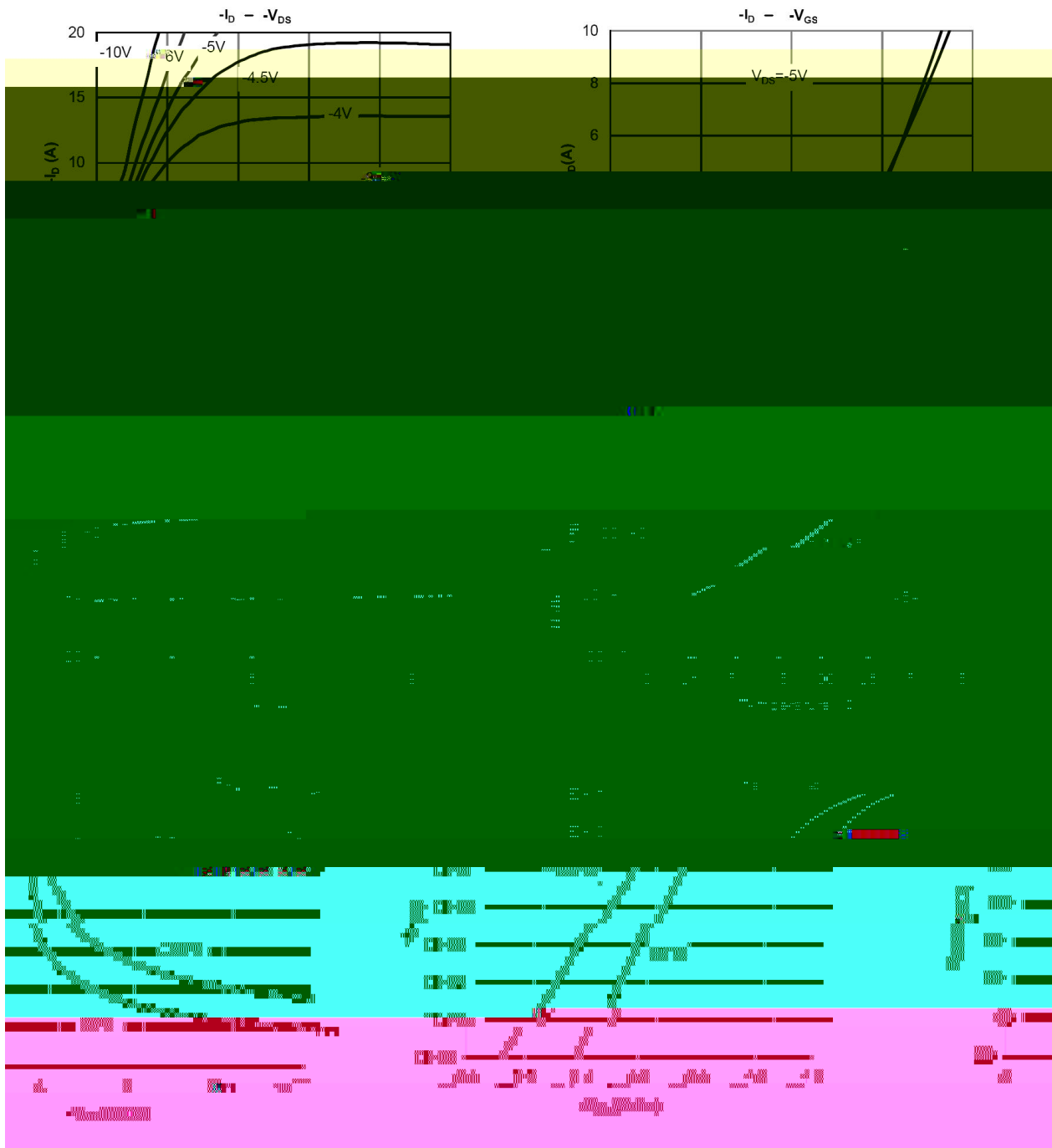
D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

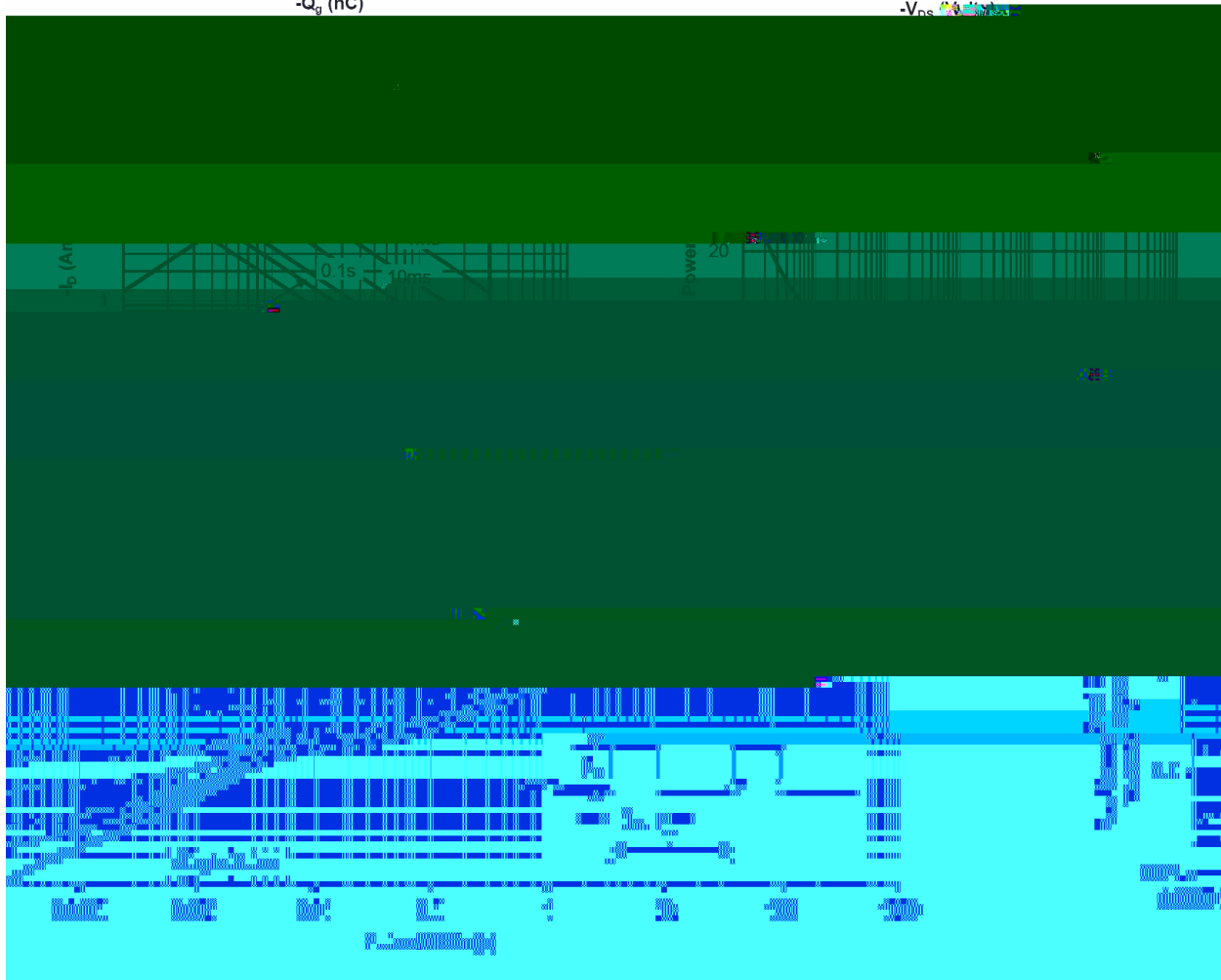
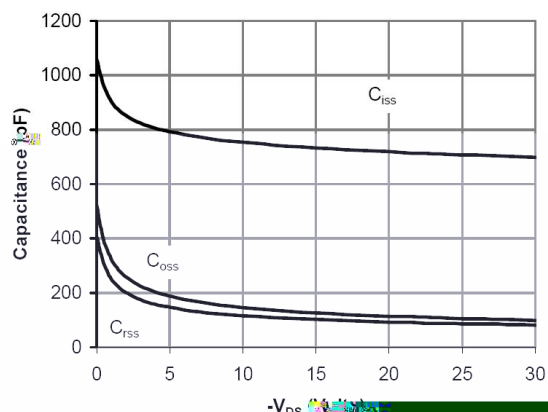
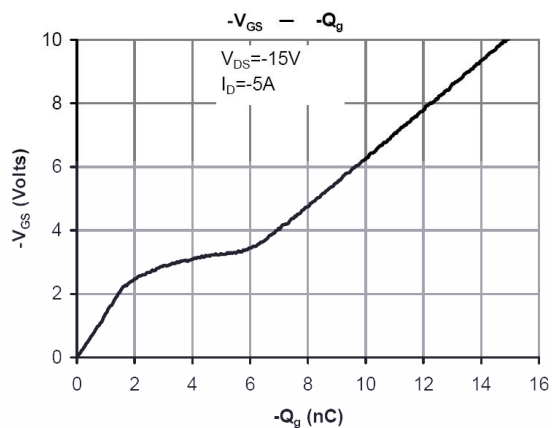
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu A$ $V_{GS}=0V$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V$ $V_{GS}=0V$			-1.0	μA
		$V_{DS}=-24V$ $V_{GS}=0V$ $T_J=55^\circ C$			-5.0	
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V$ $V_{GS}=\pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-0.5	-0.7	-1.3	V
On state drain current	$I_{D(ON)}$	$V_{GS}=-4.5V$ $V_{DS}=-5.0V$	5			A
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V$ $I_D=-5.0A$		56	65	m Ω
		$V_{GS}=-10V$ $I_D=-5.0A$ $T_J=125^\circ C$		65	86	
		$V_{GS}=-4.5V$ $I_D=-4.0A$		64	75	
Forward Transconductance	g_{FS}	$V_{DS}=-5.0V$ $I_D=-5.0A$		12		S
Diode Forward Voltage	V_{SD}	$I_S=-1.0A$ $V_{GS}=0$		-0.76	-1.0	V
Total Gate Charge(10V)	Q_g	$V_{GS}=-10V$ $V_{DS}=-15V$ $I_D=-5.0A$		14.7		nC
Total Gate Charge(4.5V)				7.6		
Gate-Source Charge	Q_{gs}			2.0		
Gate-Drain Charge	Q_{gd}			3.8		
Gate Resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		10		Ω
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=-15V$ $f=1MHz$		700		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			75		
Turn-on Delay Time	$t_{d(ON)}$	$V_{GS}=-10V$ $V_{DS}=-15V$ $R_L=3.0\Omega$ $R_{GEN}=3.0\Omega$		8.3		ns
Turn-on Rise Time	t_r			5.0		
Turn-off Delay Time	$t_{d(OFF)}$			29		
Turn-off Fall Time	t_f			14		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=-5.0A$ $di/dt=100A/\mu s$		23.5		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=-5.0A$ $di/dt=100A/\mu s$		13.4		nC

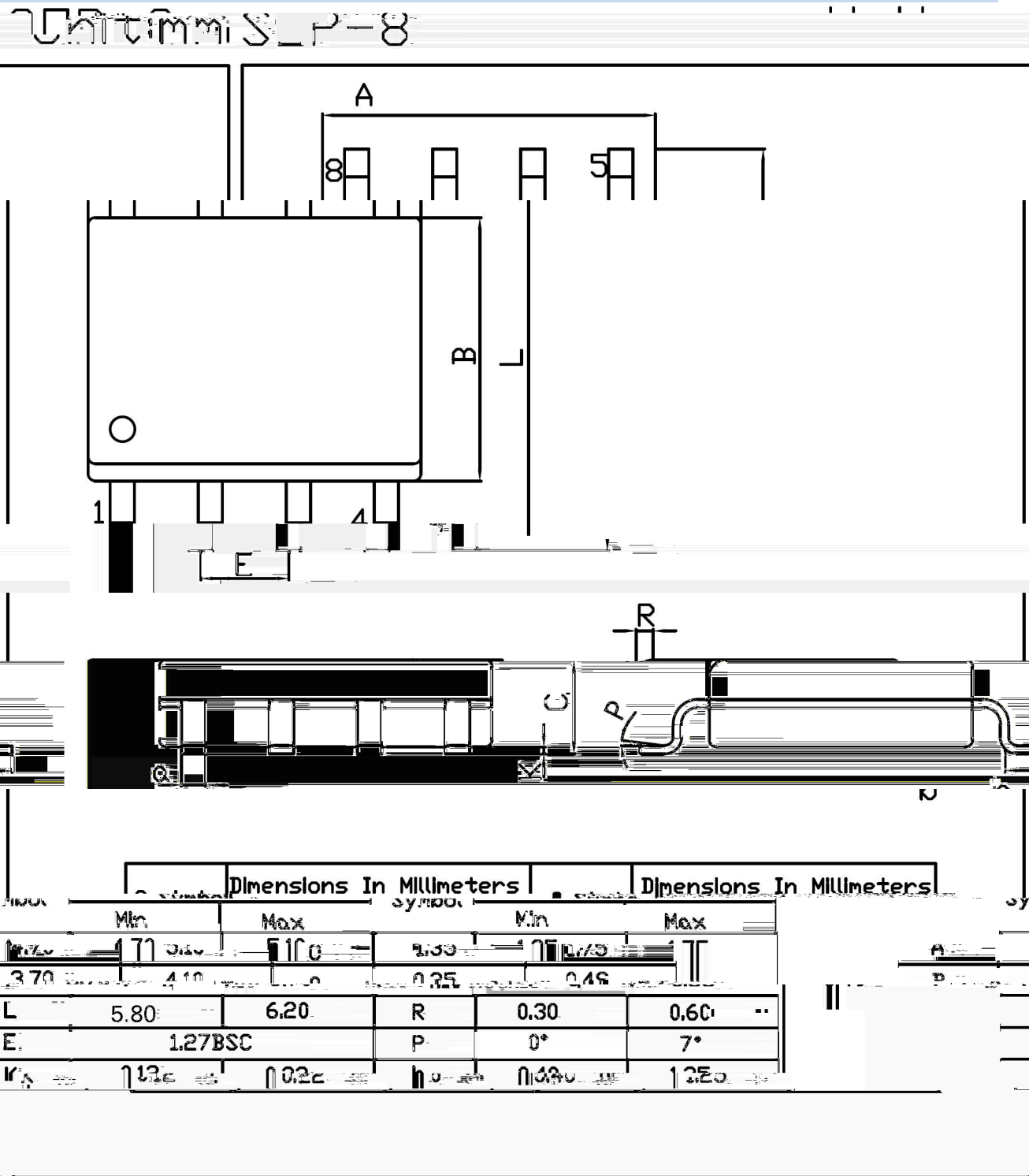
/ Electrical Characteristic Curve



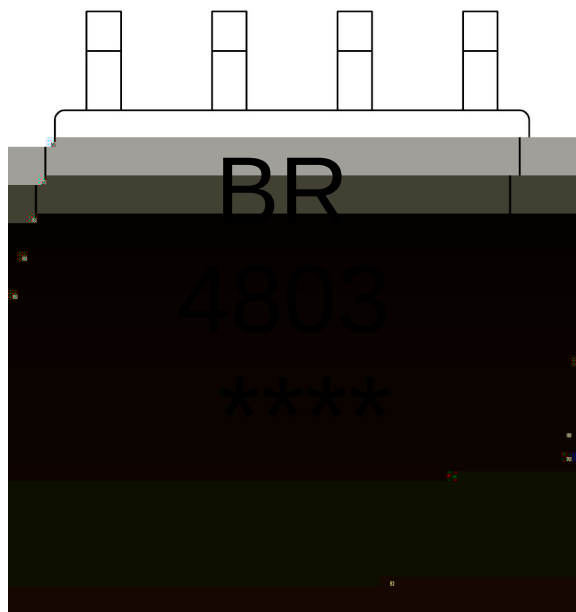
Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

4803

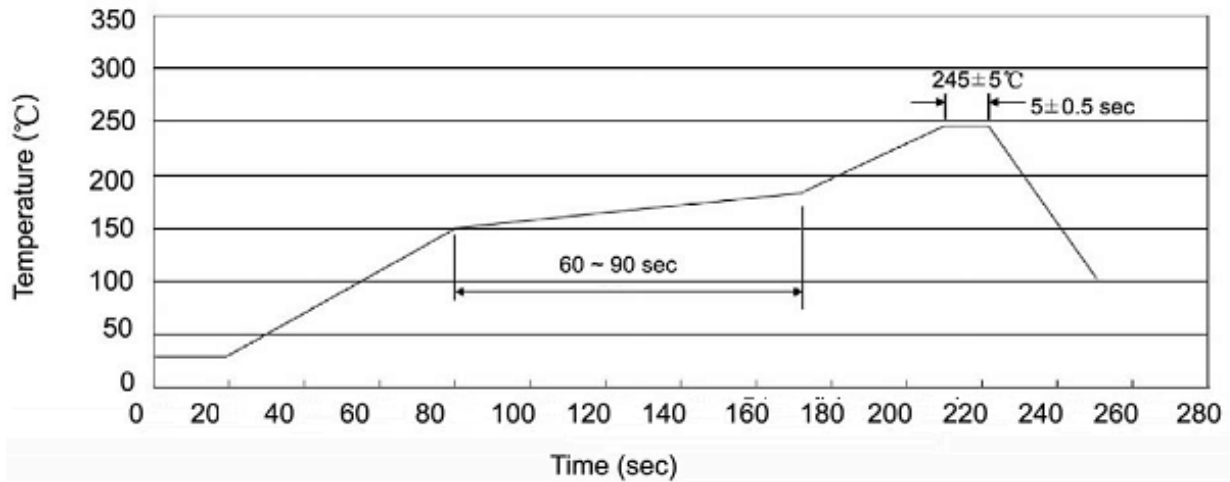
Note:

BR: Company Code.

4803: Product Type

****: Lot No. Code, code change with Lot No.

() / **Temperature Profile for IR Reflow Soldering(Pb-Free)**



Note:

- | | | | | | |
|---|-------|-----|-----------|----------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ **Resistance to Soldering Heat Test Conditions**

260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ **Packaging SPEC.**

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOP/ESOP-8	4,000	2	8,000	6	48,000	13" ×12	360×360×50	380×335×366

/ **Notices**